	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	76786	MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:36
2	BRS	L2	3633	"drift region"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:24
3	BRS	L3	90758	trench	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:25
4	BRS	L4	76574	"drain region"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:25
5	BRS	L5	150167	"gate electrode"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:26

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	L6	457	1 and 2 and 3 and 4 and 5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:26
7	BRS	L7	254	6 and ((@ad<"20010530") or (@rlad<"20010530"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:48
8	BRS	L8	16486	"withstand voltage"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:31
9	BRS	L9	350124	pitch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:31
10	BRS	L10	2	7 and 8 and 9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:31

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	84529	MOSFET or IGFET or "insulated gate field effect transistor"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:37
12	BRS	L12	14	2 same 3 same 8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:42
13	IS&R	L13	1767	(438/270).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:42
14	IS&R	L14	93	(438/272).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:42
15	BRS	L16	1801	13 or 14	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:43

	Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L17	105	16 and 2 and 3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:43
17	BRS	L18	63	17 and ((@ad<"20010530") or (@rlad<"20010530"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:53
18	IS&R	L19	2	("6316807").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/12/08 14:54